

# Plastic Medium-Power PNP Silicon Transistors

... designed for use in general-purpose amplifier and switching circuits. Recommended for use in 5 to 20 Watt audio amplifiers utilizing complementary symmetry circuitry.

• DC Current Gain —

hFE = 40 (Min) @ IC = 1.0 Adc

• MJE371 is Complementary to NPN MJE521

#### **MAXIMUM RATINGS**

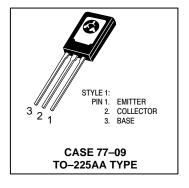
Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	40	Vdc
Collector–Base Voltage	V <sub>CB</sub>	40	Vdc
Emitter–Base Voltage	VEB	4.0	Vdc
Collector Current — Continuous — Peak	IC	4.0 8.0	Adc
Base Current — Continuous	lΒ	2.0	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	40 320	Watts mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θJC	3.12	°C/W

## **MJE371**

4 AMPERE
POWER TRANSISTOR
PNP SILICON
40 VOLTS
40 WATTS



#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS						
Collector–Emitter Sustaining Voltage (1) (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0)	VCEO(sus)	40	_	Vdc		
Collector–Base Cutoff Current (V <sub>CB</sub> = 40 Vdc, I <sub>E</sub> = 0)	ICBO	_	100	μAdc		
Emitter–Base Cutoff Current (V <sub>EB</sub> = 4.0 Vdc, I <sub>C</sub> = 0)	IEBO	_	100	μAdc		
ON CHARACTERISTICS						
DC Current Gain (1) (I <sub>C</sub> = 1.0 Adc, V <sub>CE</sub> = 1.0 Vdc)	h <sub>FE</sub>	40	_	_		

<sup>(1)</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

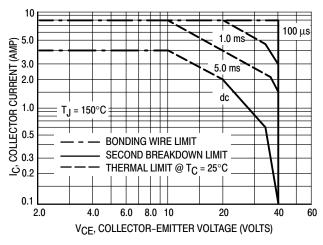
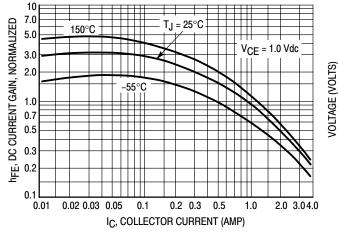


Figure 1. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_{\hbox{\scriptsize C}}-V_{\hbox{\scriptsize CE}}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on  $T_{J(pk)} = 150^{\circ}C$ ;  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ . At high case temperatures, thermal limitations will reduce the power that can be handled to values less then the limitations imposed by second breakdown.



2.0

1.6

T<sub>J</sub> = 25°C

1.2

0.8

V<sub>BE</sub>(sat) @ I<sub>C</sub>/I<sub>B</sub> = 10

V<sub>CE</sub>(sat) @ I<sub>C</sub>/I<sub>B</sub> = 10

0.005 0.01 0.02 0.03 0.05 0.1 0.2 0.3 0.5 1.0 2.0 3.04.0

I<sub>C</sub>, COLLECTOR CURRENT (AMP)

Figure 2. DC Current Gain

Figure 3. "On" Voltage

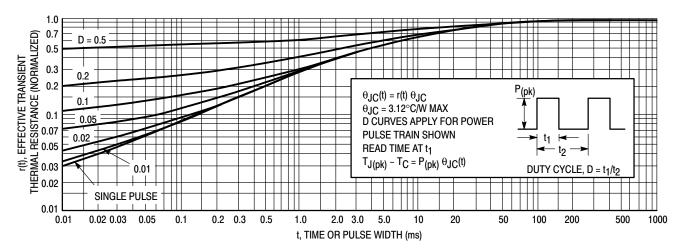
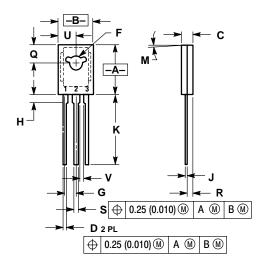


Figure 4. Thermal Response

### **MJE371**

#### **PACKAGE DIMENSIONS**

#### TO-225AA **CASE 77-09 ISSUE W**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.425	0.435	10.80	11.04
В	0.295	0.305	7.50	7.74
С	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
Н	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040		1.02	

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. BASE

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